



PHASE CONTROL DIODE MODULES

M2D-160, M2DC-160, M2DA-160

- ◆ $V_{RRM} = \underline{2400 - 3200 V}$
- ◆ $I_{F(AV)} = \underline{180 A}$ ($T_C = 85\text{ }^\circ\text{C}$)
- ◆ $I_{FSM} = \underline{5,5 kA}$ ($T_{Vj} = 125\text{ }^\circ\text{C}$)

- ◆ Heat transfer through AlN ceramic isolated metal baseplate
- ◆ Presspack construction
- ◆ High reliability at thermal cycles (10^5 at $\Delta T_C = 70\text{ }^\circ\text{C}$)
- ◆ Case width 34 mm



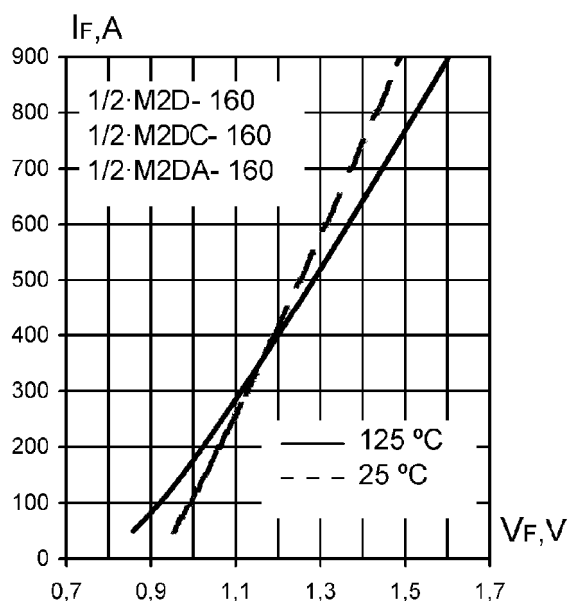
MAXIMUM RATED VALUES

| Parameter and conditions | Symbol | Values | | | Units |
|--|-------------|--------|------|-------|-----------------------|
| | | min. | typ. | max. | |
| Repetitive peak reverse voltage, $T_{Vj} = -60\text{ }^\circ\text{C} \dots +125\text{ }^\circ\text{C}$ | V_{RRM} | 2400 | - | 3200 | V |
| Non- repetitive peak reverse voltage, $T_{Vj} = -60\text{ }^\circ\text{C} \dots +125\text{ }^\circ\text{C}$ | V_{RSM} | 2500 | - | 3300 | |
| Repetitive peak reverse current, $T_{Vj} = 125\text{ }^\circ\text{C}, V_R = V_{RRM}$ | I_{RRM} | - | - | 40 | mA |
| Max. average forward current, $f = 50\text{ Hz},$ $T_C = 85\text{ }^\circ\text{C}$ | $I_{F(AV)}$ | - | - | 180 | A |
| RMS forward current | I_{FRMS} | - | - | 280 | |
| Surge forward current, $V_R = 0, T_{Vj} = 125\text{ }^\circ\text{C}, t_p = 10\text{ ms}$ | I_{FSM} | - | - | 5,5 | kA |
| Safety factor | I^2t | - | - | 150 | kA^2s |
| Operation junction temperature range | T_{Vj} | - 60 | - | + 125 | $^\circ\text{C}$ |
| Storage temperature range | T_{stg} | - 60 | - | + 50 | |

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| ELECTRICAL CHARACTERISTICS | | | | | |
|--|------------|---|-----|--------------|------------------|
| Maximum peak forward voltage, $I_F = 500 \text{ A}$, $T_{Vj} = 25 \text{ }^\circ\text{C}$ | V_{FM} | - | - | 1,25 | V |
| Threshold voltage, $T_{Vj} = 125 \text{ }^\circ\text{C}$, $I_F = 200 - 800 \text{ A}$ | $V_{(TO)}$ | - | - | 0,85 | |
| Slope resistance, $T_{Vj} = 125 \text{ }^\circ\text{C}$, $I_F = 200 - 800 \text{ A}$ | r_T | - | - | 0,85 | mΩ |
| Recovery charge, $di_F/dt = -5 \text{ A}/\mu\text{s}$, $T_{Vj} = 125 \text{ }^\circ\text{C}$, $I_F = 160 \text{ A}$, $V_R \geq 100 \text{ V}$ | Q_{rr} | - | - | 1000 | μAs |
| Insulation test voltage (RMS), $f = 50 \text{ Hz}$, $t = 1\text{sec}/1\text{min}$ | V_{isol} | - | - | 3600/3000 | V |
| THERMAL PARAMETERS | | | | | |
| Thermal resistance junction to case, per diode per module | R_{thjc} | - | - | 0,18 0,09 | °C/W |
| Thermal resistance case to heatsink, per diode per module | R_{thch} | - | - | 0,10 0,05 | |
| MECHANICAL PARAMETERS | | | | | |
| Weight | w | - | 0,5 | - | kg |
| Terminal connection torque | M_t | 4 | - | 6 | Nm |
| Heatsink mounting torque | M_s | 4 | - | 6 | |
| Maximum acceleration (at nominal mounting force) | a | - | - | 50 | m/s ² |

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forward characteristics model

$$V_F = A + B \cdot I_F + C \cdot \ln(I_F + 1) + D \cdot \sqrt{I_F}$$

 Valid for $I_F = 50 - 900$ A

| | $T_{Vj} = 125$ °C | $T_{Vj} = 25$ °C |
|---|-------------------|------------------|
| A | 0.711 | 0.896 |
| B | 0.0006755 | 0.0005074 |
| C | 0.02 | -0.0004827 |
| D | 0.004938 | 0.004717 |

Fig. 1. Maximum forward characteristics
(Limit device, 10 ms, half sine)

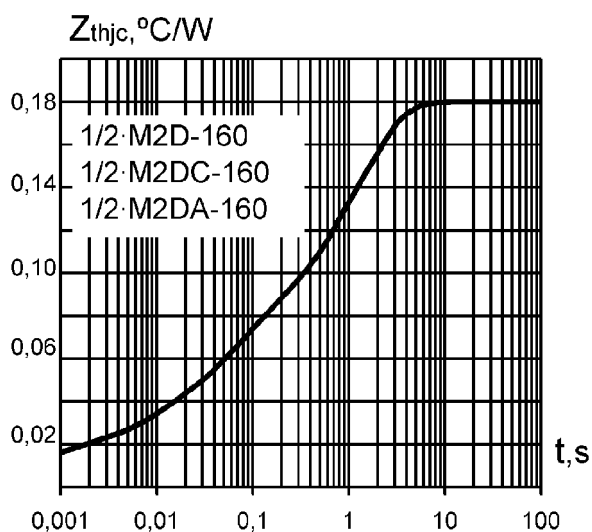


Fig. 2. Transient thermal impedance junction to case (DC)



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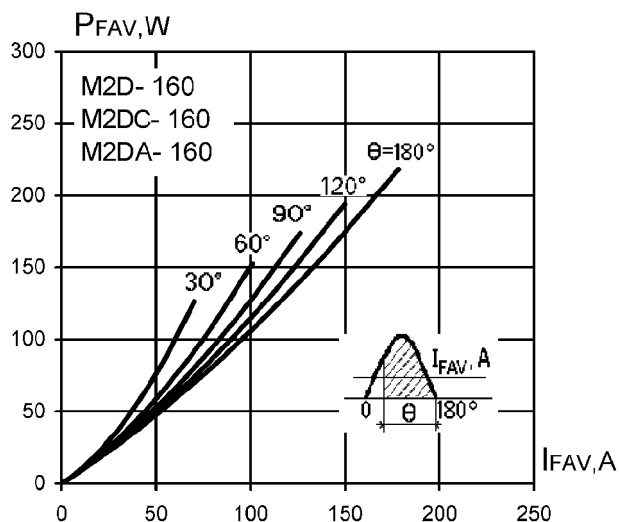


Fig. 3. Power loss vs. forward current
(sine)

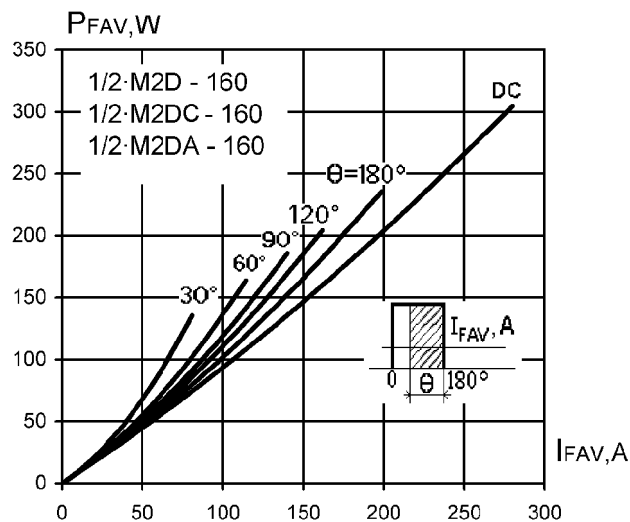


Fig. 4. Power loss vs. forward current
(rectangular)

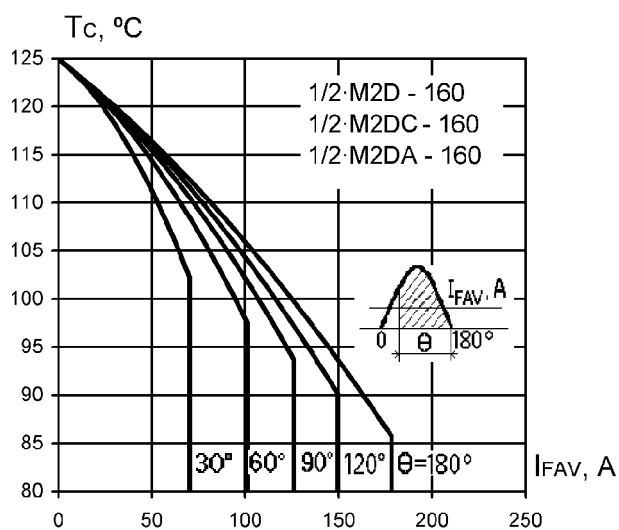


Fig. 5. Maximum allowable case temperature vs.
forward current
(sine)

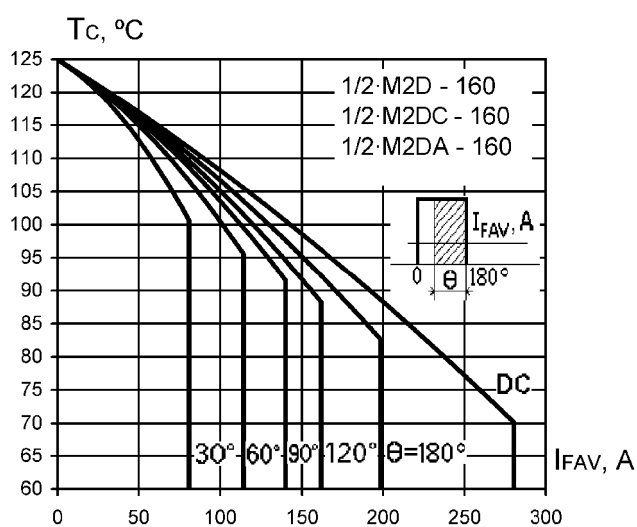


Fig. 6. Maximum allowable case temperature vs.
forward current
(rectangular)

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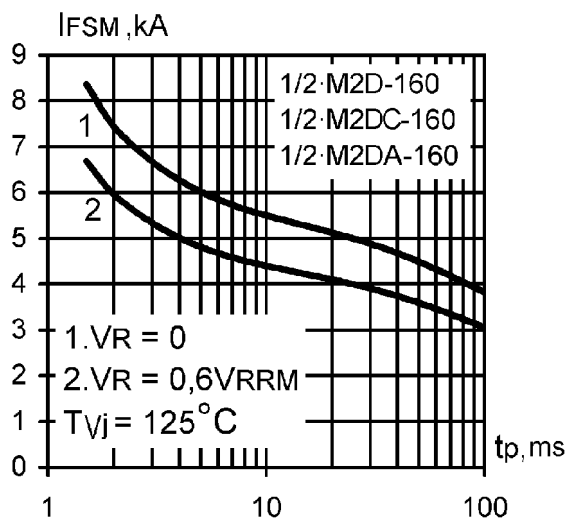


Fig. 7. Surge current vs. pulse length
(half-sine)

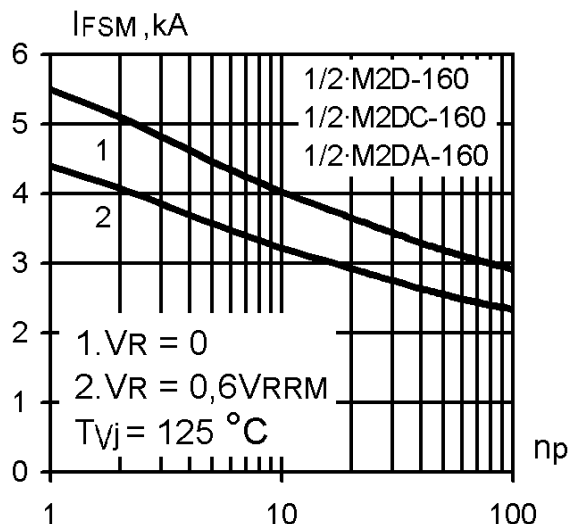


Fig. 8. Surge current vs. number of pulses
(half-sine, 10 ms, 50 Hz)

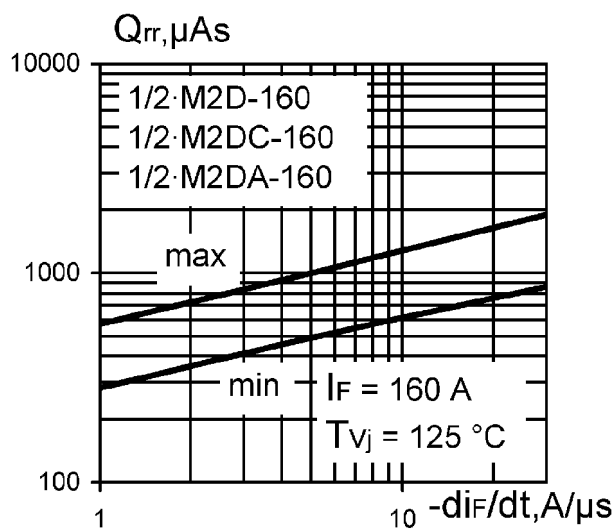


Fig. 9. Recovery charge vs. decay rate current

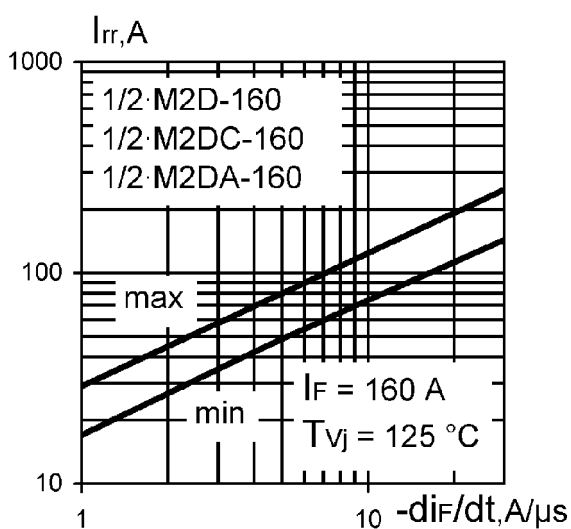


Fig. 10. Peak reverse recovery current vs. decay rate current

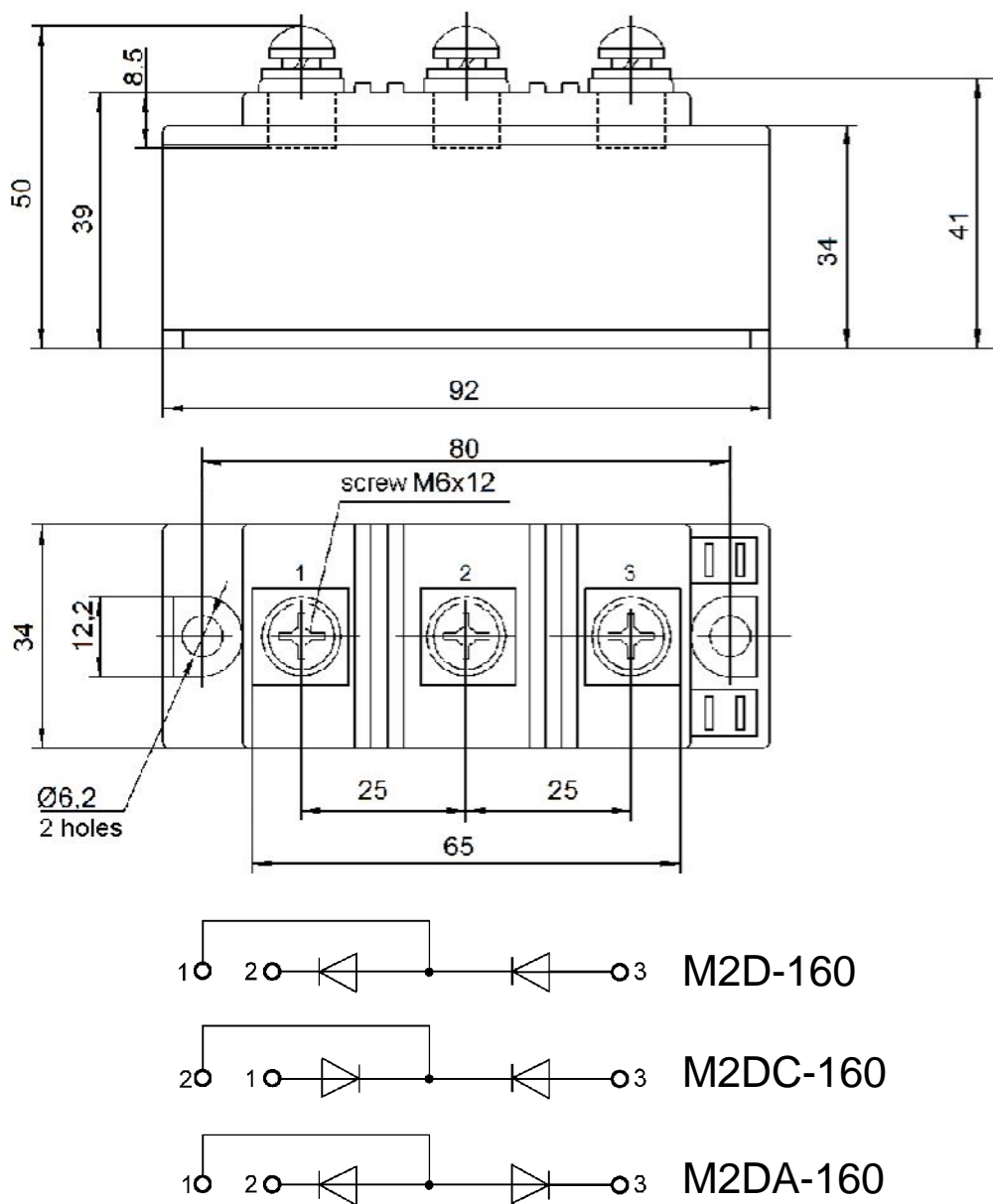
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Fig. 11. Device Outline Drawing
(dimensions in mm)

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